



BYW98-200

HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODES

MAIN PRODUCT CHARACTERISTICS

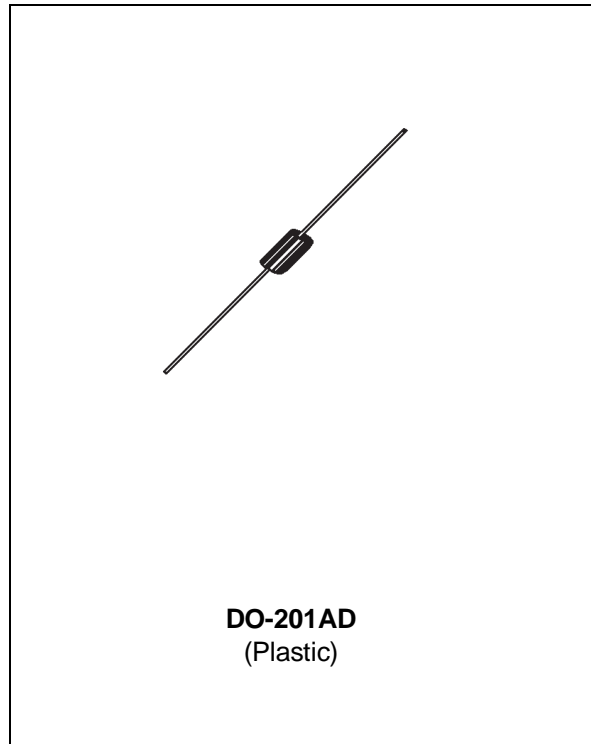
$I_{F(AV)}$	3A
V_{RRM}	200 V
$T_j(max)$	150 °C
$V_F(max)$	0.85 V
$t_{rr}(max)$	35 ns

FEATURES AND BENEFITS

- VERY LOW CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD AND REVERSE RECOVERY TIMES

DESCRIPTION

Low voltage drop and rectifier suited for switching mode base drive and transistor circuits.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		200	V
I_{FRM}	Repetitive peak forward current *	$t_p=5 \mu s$ $F=1KHz$	110	A
$I_F(AV)$	Average forward current*	$T_a = 75^\circ C$ $\delta = 0.5$	3	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10ms$ Sinusoidal	70	A
T_{stg}	Storage temperature range		- 65 to + 150	°C
T_j	Maximum operating junction temperature		150	°C
T_L	Maximum lead temperature for soldering during 10s at 4mm from case		230	°C

* On infinite heatsink with 10mm lead length.

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THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
Rth (j-a)	Junction-ambient *	25	°C/W

* On infinite heatsink with 10mm lead length.

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
I _R *	Reverse leakage current	T _j = 25°C	V _R = V _{RRM}			10	μA
		T _j = 100°C				0.5	mA
V _F **	Forward voltage drop	T _j = 25°C	I _F = 9A			1.2	V
		T _j = 100°C	I _F = 3A		0.78	0.85	

Pulse test : * tp = 5 ms, δ < 2 %

** tp = 380 μs, δ < 2 %

To evaluate the conduction losses use the following equations:

$$P = 0.75 \times I_F(AV) + 0.04 I_F^2(RMS)$$

RECOVERY CHARACTERISTICS

Symbol	Test Conditions	Min.	Typ.	Max.	Unit
t _{rr}	T _j = 25°C V _R = 30V I _F = 1A di _F /dt = - 50A/μs			35	ns
Q _{rr}	T _j = 25°C V _R ≤ 30V I _F = 3A di _F /dt = - 20A/μs		15		nC
t _{fr}	T _j = 25°C I _F = 3A Measured at 1.1 x V _F max di _F /dt = - 50A/μs		20		ns
V _{FP}	T _j = 25°C I _F = 3A di _F /dt = - 50A/μs		5		V

Fig. 1: Average forward power dissipation versus average forward current.

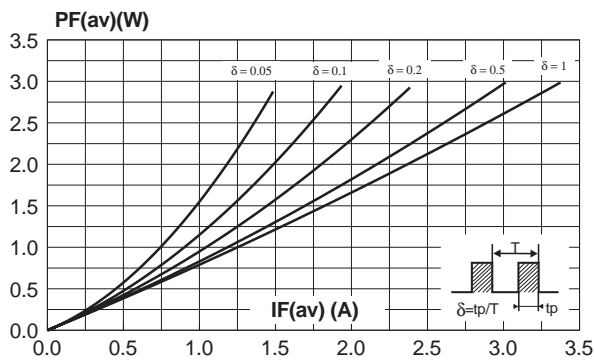


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$).

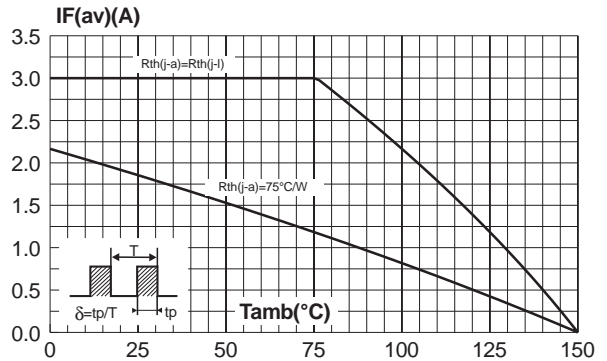


Fig. 3: Thermal resistance versus lead length.

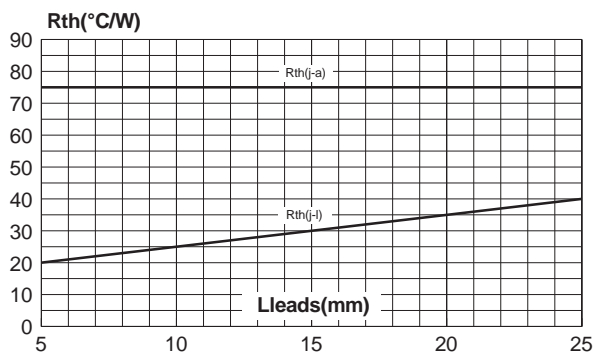


Fig. 4: Variation of thermal impedance junction to ambient versus pulse duration (recommended pad layout, epoxy FR4, $e(\text{Cu})=35\mu\text{m}$).

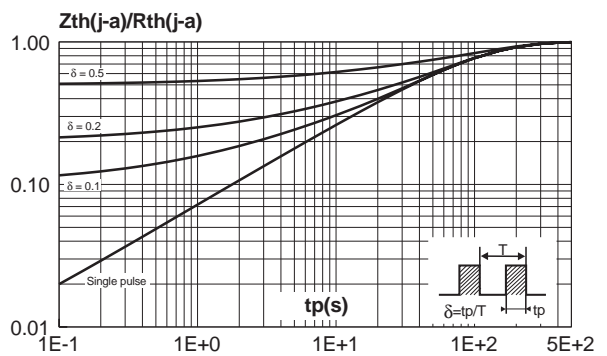


Fig. 5: Forward voltage drop versus forward current (maximum values).

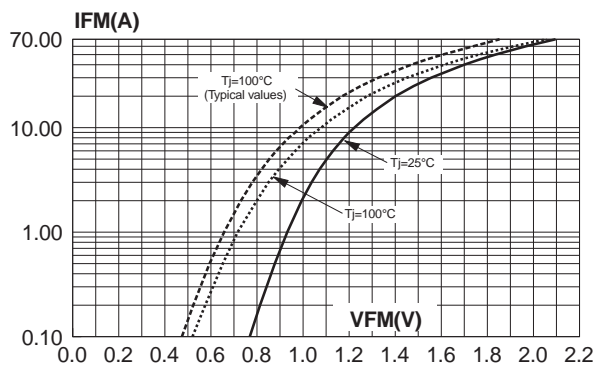


Fig. 6: Junction capacitance versus reverse voltage applied (typical values).

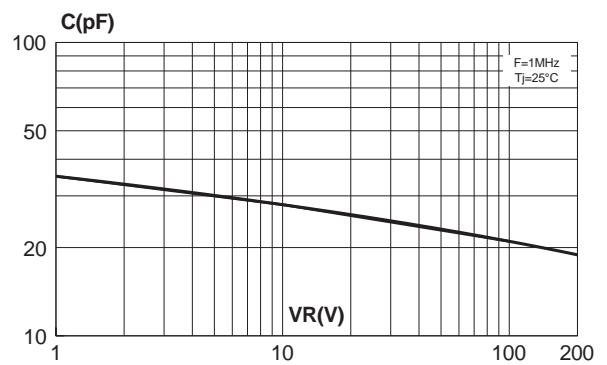


Fig. 7: Reverse recovery time versus dI_F/dt .

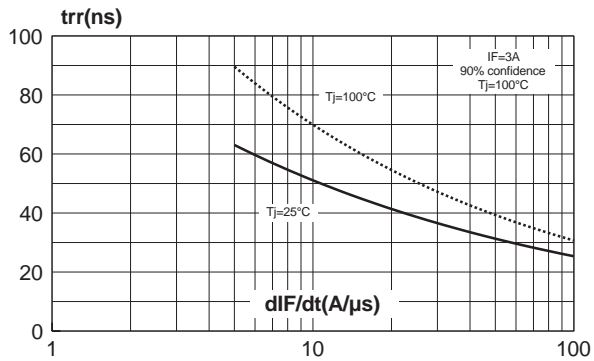


Fig. 8: Peak reverse recovery current versus dI_F/dt .

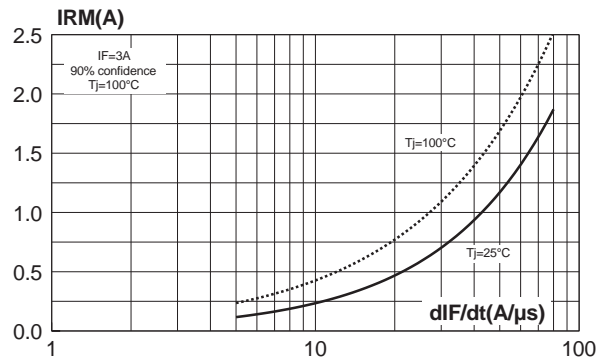
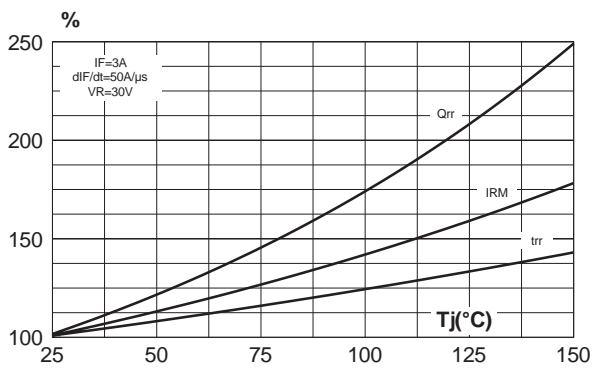
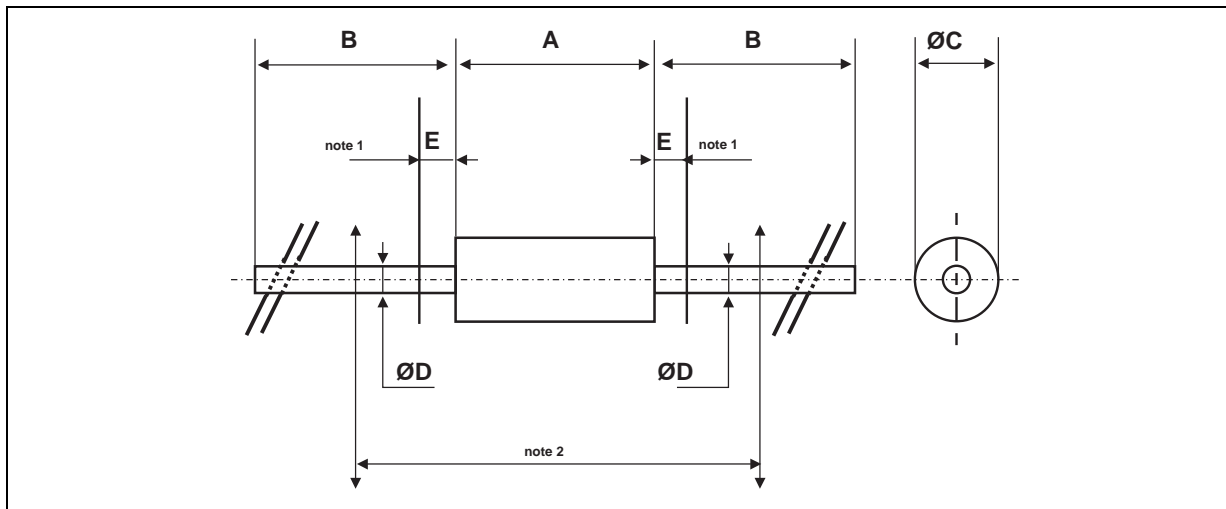


Fig. 9: Dynamic parameters versus junction temperature.



PACKAGE MECHANICAL DATA

DO-201AD



REF.	DIMENSIONS				NOTES
	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
A		9.50		0.374	1 - The lead diameter $\varnothing D$ is not controlled over zone E 2 - The minimum axial length within which the device may be placed with its leads bent at right angles is 0.59" (15 mm)
B	25.40		1.000		
$\varnothing C$		5.30		0.209	
$\varnothing D$		1.30		0.051	
E		1.25		0.049	

Ordering code	Marking	Package	Weight	Base qty	Delivery mode
BYW98-200	BYW98-200	DO-201AD	1.16 g.	600	Box
BYW98-200RL	BYW98-200	DO-201AD	1.16 g.	1900	Tape and reel

- White band indicates cathode
- Epoxy meets UL94,V0

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